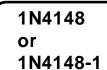
## Silicon Switching Diode



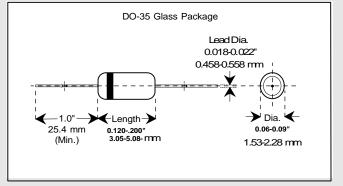
## **DO-35 Glass Package**

## **Applications**

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

## Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond<sup>™</sup> plating for problem free solderability
- LL-34/35 MELF SMD available
- Hermetic Glass Body
- Available up to JANTXV-1 levels



"S" level screening available to Source Control Drawings-

Maximum Batinga			Symbo		Unit
Maximum Ratings			Symbo		Unit
Peak Inverse Voltage			PIV	100 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			I <sub>Fdc</sub>	300	mAmps
Peak Surge Current (t <sub>peak</sub> = 1 sec.)			l <sub>peak</sub>	1.0	Amp
BKC Power Dissipation $T_L=50 \text{ °C}$ , L = 3/8" from body			P <sub>tot</sub>	500	mWatts
Operating Temperature Range			T <sub>Op</sub>	-65 to +200	° C
Storage Temperature Range			T <sub>st</sub>	-65 to +200	° C
Electrical Characteristics @ 25°C*	lectrical Characteristics @ 25 °C* Symbol M		nimum	Maximum	Unit
Forward Voltage Drop @ I <sub>F</sub> = 10 mA	V <sub>F</sub>	*	**	1.00	Volts
Breakdown Voltage @ I <sub>R</sub> = 5 µA	PIV	-	75		Volts
Breakdown Voltage @ I <sub>R</sub> =100µA	PIV	1	00		Volts
Reverse Leakage Current @ V <sub>R</sub> = 75 V	ا <sub>R</sub>			5 (100 @ 150 °C)	μA
Capacitance @ V <sub>R</sub> = 0 V, f = 1mHz	C <sub>T</sub>			4.0	рF
Reverse Recovery time (note 1)	t <sub>rr</sub>			4.0	nSecs

Note 1: Per Method 4031-A with I<sub>F</sub> = 10 mA, Vr = 6 V, R<sub>I</sub> = 100 Ohms. \* UNLESS OTHERWISE SPECIFIED

